

Radiation Hardened Quad 2-Input NAND Gate with Open Drain

January 1996

Features

- Devices QML Qualified in Accordance with MIL-PRF-38535
- Detailed Electrical and Screening Requirements are Contained in SMD# 5962-96703 and Harris' QM Plan
- 1.25 Micron Radiation Hardened SOS CMOS
- Total Dose >300K RAD (Si)
- Single Event Upset (SEU) Immunity: <1 x 10⁻¹⁰ Errors/Bit/Day (Typ)
- SEU LET Threshold >100 MEV-cm²/mg
- Dose Rate Upset >10¹¹ RAD (Si)/s, 20ns Pulse
- Dose Rate Survivability >10¹² RAD (Si)/s, 20ns Pulse
- Latch-Up Free Under Any Conditions
- Military Temperature Range -55°C to +125°C
- Significant Power Reduction Compared to ALSTTL Logic
- DC Operating Voltage Range 4.5V to 5.5V
- Input Logic Levels
 - VIL = 30% of VCC Max
 - VIH = 70% of VCC Min
- Input Current ≤ 1μA at VOL, VOH
- Fast Propagation Delay 15ns (Max), 10ns (Typ)

Description

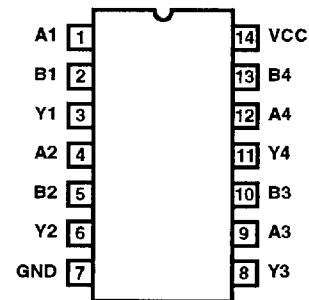
The Harris ACS03MS is a Radiation Hardened quad 2-input NAND gate with open drain outputs. The open drain output can drive resistive loads from a separate supply voltage.

The ACS03MS utilizes advanced CMOS/SOS technology to achieve high-speed operation. This device is a member of a radiation hardened, high-speed, CMOS/SOS Logic Family.

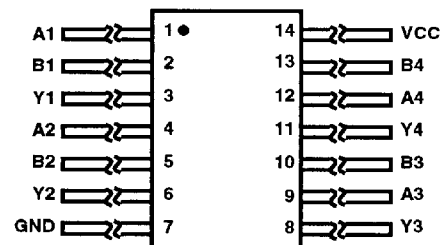
The ACS03MS is supplied in a 14 lead Ceramic Flatpack (K suffix) or a Ceramic Dual-In-Line Package (D suffix).

Pinouts

14 PIN CERAMIC DUAL-IN-LINE
MIL-STD-1835 DESIGNATOR CDIP2-T14,
LEAD FINISH C
TOP VIEW



14 PIN CERAMIC FLATPACK
MIL-STD-1835 DESIGNATOR CDFP3-F14,
LEAD FINISH C
TOP VIEW



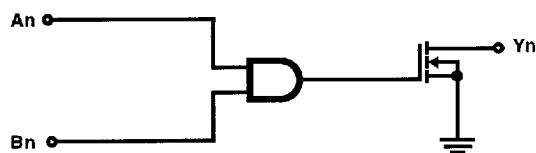
Ordering Information

PART NUMBER	TEMPERATURE RANGE	SCREENING LEVEL	PACKAGE
5962F9670301VCC	-55°C to +125°C	MIL-PRF-38535 Class V	14 Lead SBDIP
5962F9670301VXC	-55°C to +125°C	MIL-PRF-38535 Class V	14 Lead Ceramic Flatpack
ACS03D/Sample	25°C	Sample	14 Lead SBDIP
ACS03K/Sample	25°C	Sample	14 Lead Ceramic Flatpack
ACS03HMSR	25°C	Die	Die

CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures.

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Functional Diagram**TRUTH TABLE**

INPUTS		OUTPUT
An	Bn	Yn
L	L	Z (Note 2), H (Note 3)
L	H	Z (Note 2), H (Note 3)
H	L	Z (Note 2), H (Note 3)
H	H	L

NOTES:

1. L = Low, H = High, Z = High Impedance
2. Without Pull-up Resistor
3. With Pull-up Resistor

Die Characteristics

DIE DIMENSIONS:

68 mils x 79 mils
1730mm x 2010mm

METALLIZATION:

Type: AlSi
Metal 1 Thickness: $7.125\text{k}\text{\AA} \pm 1.125\text{k}\text{\AA}$
Metal 2 Thickness: $9\text{k}\text{\AA} \pm 1\text{k}\text{\AA}$

GLASSIVATION:

Type: SiO_2
Thickness: $8\text{k}\text{\AA} \pm 1\text{k}\text{\AA}$

WORST CASE CURRENT DENSITY:

$<2.0 \times 10^5 \text{A/cm}^2$

BOND PAD SIZE:

$110\mu\text{m} \times 110\mu\text{m}$
4.3 mils x 4.3 mils

Metallization Mask Layout

